Dual 4-Stage Binary Ripple Counter

High-Performance Silicon-Gate CMOS

The MC74HC393A is identical in pinout to the LS393. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of two independent 4-bit binary ripple counters with parallel outputs from each counter stage. A \div 256 counter can be obtained by cascading the two binary counters.

Internal flip—flops are triggered by high—to—low transitions of the clock input. Reset for the counters is asynchronous and active—high. State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used as clocks or as strobes except when gated with the Clock of the HC393A.

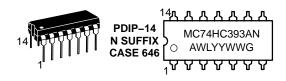
Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- Chip Complexity: 236 FETs or 59 Equivalent Gates
- Pb–Free Packages are Available*



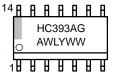
http://onsemi.com

MARKING DIAGRAMS





SOIC-14 D SUFFIX CASE 751A

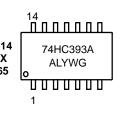




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb−Free Package
■ Pb−Free Package

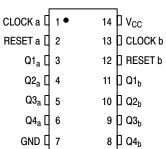
(Note: Microdot may be in either location)

ORDERING INFORMATION

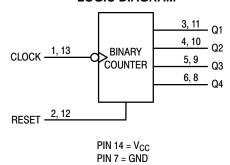
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PIN ASSIGNMENT



LOGIC DIAGRAM



FUNCTION TABLE

Inp		
Clock	Reset	Outputs
Х	Н	L
Н	L	No Change
L	L	No Change
	L	No Change
	L	Advance to Next State

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC393AN	PDIP-14	500 Units / Rail
MC74HC393ANG	PDIP-14 (Pb-Free)	500 Units / Rail
MC74HC393AD	SOIC-14	55 Units / Rail
MC74HC393ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC393ADR2	SOIC-14	2500 Units / Reel
MC74HC393ADR2G	SOIC-14 (Pb-Free)	2500 Units / Reel
MC74HC393ADTR2	TSSOP-14*	2500 Units / Reel
MC74HC393ADTR2G	TSSOP-14*	2500 Units / Reel
MC74HC393AFEL	SOEIAJ-14	2000 Units / Reel
MC74HC393AFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb–Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V _{CC}	>
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	V _{CC} : (Figure 1)	= 2.0 V = 3.0 V = 4.5 V = 6.0 V	0 0 0	1000 600 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad I_{out} \le 2.4 \text{ mA} $ $ I_{out} \le 4.0 \text{ mA} $ $ I_{out} \le 5.2 \text{ mA} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{out}} \leq 2.4 \text{ mA} \\ I_{\text{out}} \leq 4.0 \text{ mA} \\ I_{\text{out}} \leq 5.2 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 3)	2.0 3.0 4.5 6.0	10 15 30 50	9 14 28 45	8 12 25 40	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q1 (Figures 1 and 3)	2.0 3.0 4.5 6.0	70 40 24 20	80 45 30 26	90 50 36 31	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q2 (Figures 1 and 3)	2.0 3.0 4.5 6.0	100 56 34 20	105 70 45 38	180 100 55 48	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q3 (Figures 1 and 3)	2.0 3.0 4.5 6.0	130 80 44 37	150 105 55 47	180 130 70 58	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q4 (Figures 1 and 3)	2.0 3.0 4.5 6.0	160 110 52 44	250 185 65 55	300 210 82 65	ns
t _{PHL}	Maximum Propagation Delay, Reset to any Q (Figures 2 and 3)	2.0 3.0 4.5 6.0	80 48 30 26	95 65 38 33	110 75 50 43	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

NOTES:

^{2.} Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_PD	Power Dissipation Capacitance (Per Counter)*	35	pF

^{*}Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

^{1.} For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	25 15 10 9	30 20 13 11	40 30 15 13	ns
t _w	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 15	110 36 22 19	ns
t _w	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 15	110 36 22 19	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS Clock (Pins 1, 13)

Clock input. The internal flip-flops are toggled and the counter state advances on high-to-low transitions of the clock input.

OUTPUTS

Q1, Q2, Q3, Q4 (Pins 3, 4, 5, 6, 8, 9, 10, 11)

Parallel binary outputs Q4 is the most significant bit.

CONTROL INPUTS Reset (Pins 2, 12)

Active-high, asynchronous reset. A separate reset is provided for each counter. A high at the Reset input prevents counting and forces all four outputs low.

SWITCHING WAVEFORMS

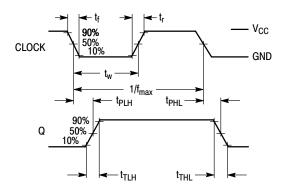
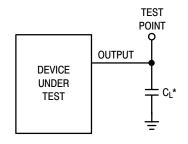


Figure 1.



*Includes all probe and jig capacitance

Figure 3. Test Circuit

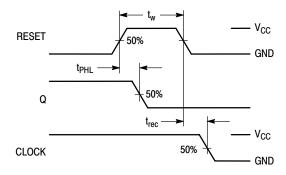
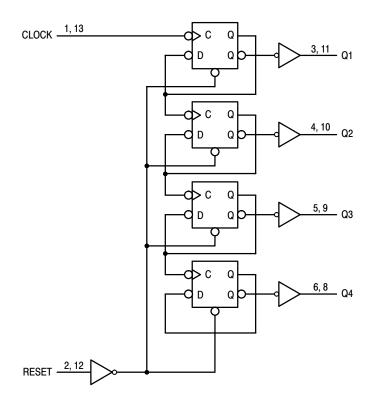
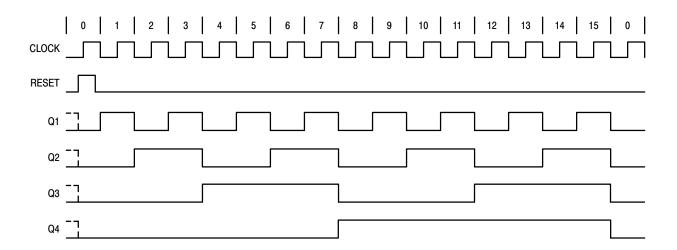


Figure 2.

EXPANDED LOGIC DIAGRAM



TIMING DIAGRAM

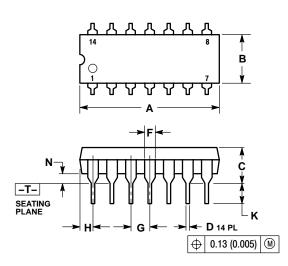


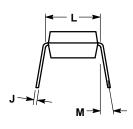
COUNT SEQUENCE

	Outputs				
Count	Q4	Q3	Q2	Q1	
0	L	L	L	L	
1	L	L	L	Н	
2	L	L	Н	L	
3	L	L	Н	Н	
4	L	Н	L	L	
5	L	Н	L	Н	
6	L	Н	Н	L	
7	L	Н	Н	Н	
8	Н	L	L	L	
9	Н	L	L	Н	
10	Н	L	Н	L	
11	Н	L	Н	Н	
12	Н	Н	L	L	
13	Н	Н	L	Н	
14	Н	Н	Н	L	
15	Н	Н	Н	Н	

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 **ISSUE N**





NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.

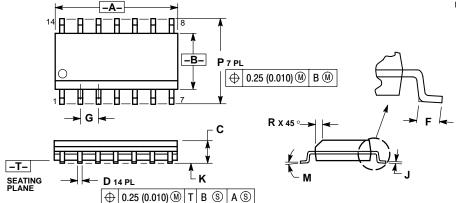
 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEADS
 WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	18.80
В	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	0.100 BSC		BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10 °		10 °
N	0.015	0.039	0.38 1.01	

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE G**



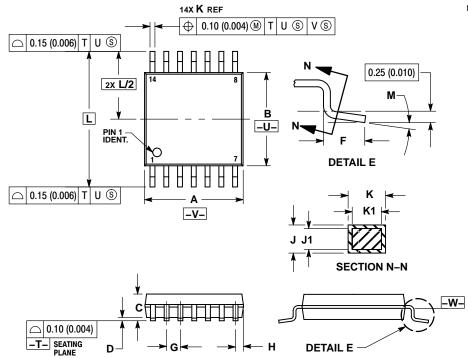
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAAIMUM MOLD PROTRUSION 0.15 (0.0)
 PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	1.27 BSC		BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 - (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 - DIMENSION AT MAXIMUM MATERIAL CONDITION.

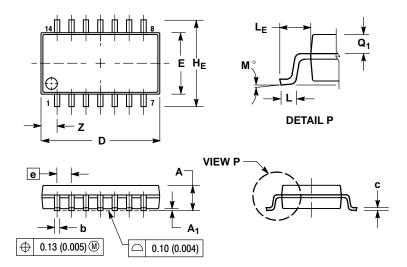
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8 °	0°	8 °

PACKAGE DIMENSIONS

SOEIAJ-14 **F SUFFIX** CASE 965-01 **ISSUE O**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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